

STB40NF10L

N-channel 100V - 0.028Ω - 40A - D²PAK Low gate charge STripFET™ II Power MOSFET

General features

Туре	V _{DSS}	R _{DS(on)}	I _D
STB40NF10L	100V	<0.033Ω	40A

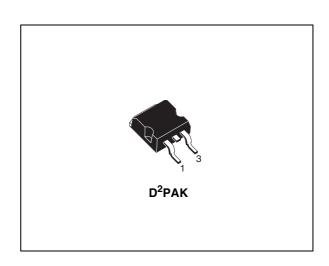
- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

Description

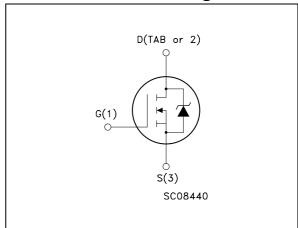
This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced highefficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

Applications

■ Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging	
STB40NF10L	B40NF10L	D ² PAK	Tape & reel	

Contents STB40NF10L

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STB40NF10L Electrical ratings

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V _{GS} = 0)	100	V
V_{DGR}	Drain-gate voltage (R _{GS} = 20 kΩ)	100	V
V_{GS}	Gate- source voltage	± 15	V
I _D	Drain current (continuous) at T _C = 25°C	40	Α
I _D	Drain current (continuous) at T _C = 100°C	25	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	160	Α
P _{tot}	Total dissipation at T _C = 25°C	150 W	
	Derating Factor	1	W/°C
E _{AS} (2)	Single pulse avalanche energy 430		mJ
T _{stg}	Storage temperature		°C
Tj	Max. operating junction temperature	-65 to 175 °C	

^{1.} Pulse width limited by safe operating area.

Table 2. Thermal data

Rthj-case	Thermal resistance junction-case max	1	°C/W
Rthj-amb	Thermal resistance junction-ambient max	62.5	°C/W
T_J	T _J Maximum lead temperature for soldering purpose		°C

^{2.} Starting $T_j = 25$ °C, $I_D = 20A$, $V_{DD} = 40V$

Electrical characteristics STB40NF10L

2 Electrical characteristics

(T_{CASE} =25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter Test conditions		Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	100			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = Max rating V_{DS} = Max rating, T_{C} = 125°C			1 10	μ Α μ Α
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.7	2.5	V
R _{DS(on)}	Static drain-source on resistance	$V_{GS} = 10V, I_D = 20A$ $V_{GS} = 5V, I_D = 20A$		0.028 0.030	0.033 0.036	Ω Ω

Table 4. Dynamic

4/13

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 _{fs} (1)	Forward transconductance	$V_{DS} = 15V_{,} I_{D} = 20A$		25		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		2300 290 125		pF pF pF
$\begin{array}{c} t_{\text{d(on)}} \\ t_{\text{r}} \\ t_{\text{d(off)}} \\ t_{\text{f}} \end{array}$	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 50V, I_D = 20A R_G = 4.7 Ω V_{GS} = 4.5V (see <i>Figure 13</i>)		25 82 64 24		ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 80V, I_{D} = 40A, V_{GS} = 4.5V, R_{G} = 4.7 Ω (see <i>Figure 14</i>)		46 12 22	64	nC nC nC

^{1.} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

Table 5. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)				40 160	A A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 40A, V _{GS} = 0			1.3	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 40A$, di/dt = 100A/ μ s, $V_{DD} = 30V$, $T_{j} = 150$ °C (see <i>Figure 15</i>)		110 467 8		ns nC A

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

Electrical characteristics STB40NF10L

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Thermal impedance

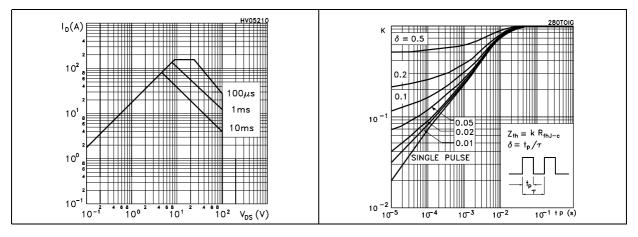


Figure 3. Output characterisics

Figure 4. Transfer characteristics

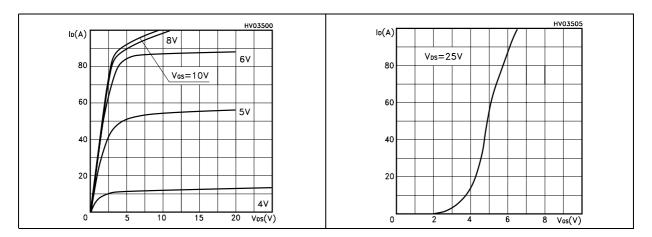


Figure 5. Transconductance

Figure 6. Static drain-source on resistance

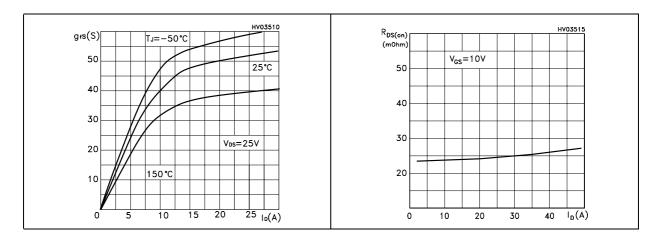
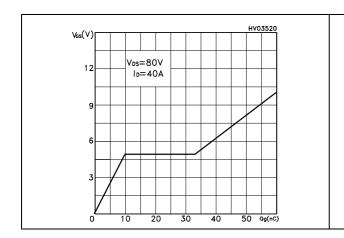


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations



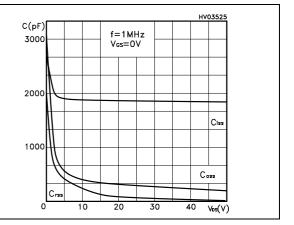
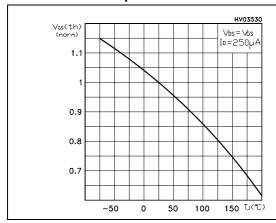


Figure 9. Normalized gate threshold voltage vs temperature

Figure 10. Normalized on resistance vs temperature



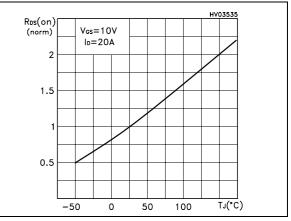
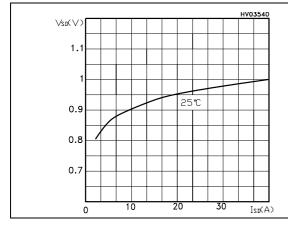
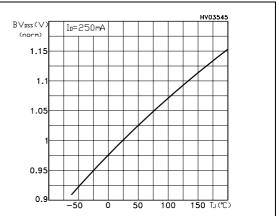


Figure 11. Source-drain diode forward characteristics

Figure 12. Normalized breakdown voltage vs temperature





Test circuit STB40NF10L

3 Test circuit

Figure 13. Switching times test circuit for resistive load

Figure 14. Gate charge test circuit

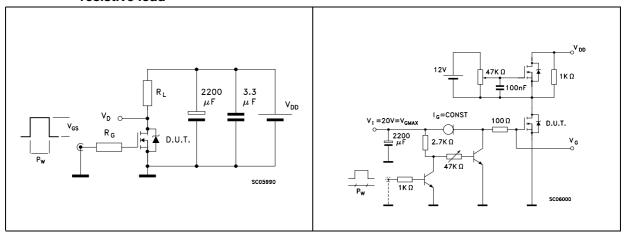


Figure 15. Test circuit for inductive load switching and diode recovery times

Figure 16. Unclamped Inductive load test circuit

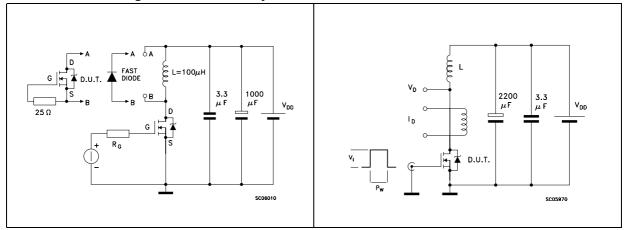
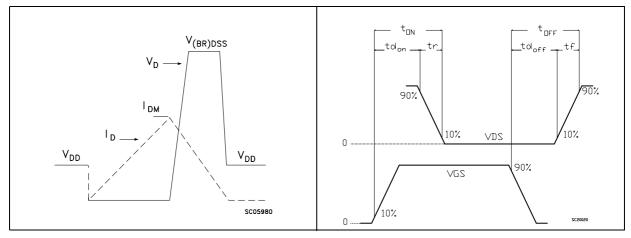


Figure 17. Unclamped inductive waveform

Figure 18. Switching time waveform

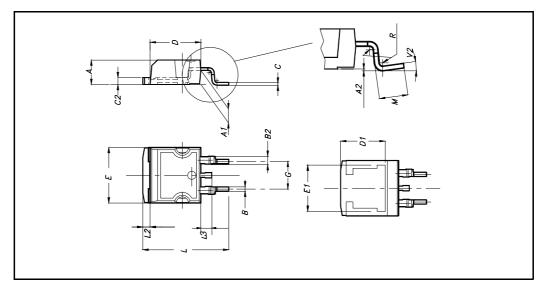


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

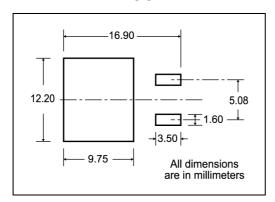
D²PAK MECHANICAL DATA

DIM.	mm.				inch	
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0 _δ		4º			

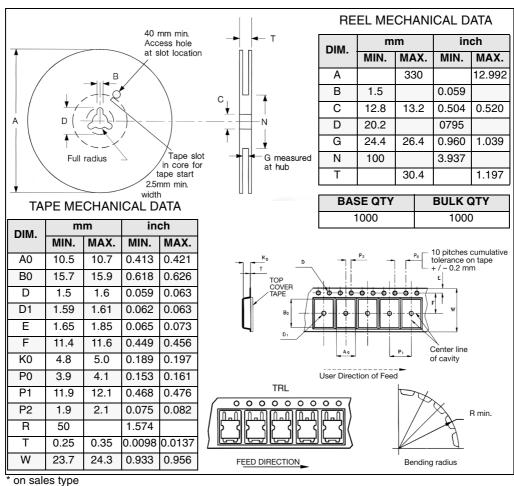


Packing mechanical data 5

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



Revision history STB40NF10L

6 Revision history

Table 6. Revision history

Date	Revision	Changes	
21-Jun-2004	1	First release	
26-Jun-2006	2	New template, no content change	

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